

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7	("5480048" "5600103" "5970319" "6930388").PN. and (conduct\$4 or metal) with (substrate or wafer or carrier or base or plate or support)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/07 09:30
L2	2	("5480048" "5600103" "5970319" "6930388").PN. and (conduct\$4 or metal) with (substrate or wafer or carrier or base or plate or support) and (insulat\$4 or oxide or dielectric) and press \$4 with (insulat\$4 or oxide or dielectric)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/07 09:32
S1	0	((("JP2001-537286") or ("JP2001-68850") or ("JP7-111375") or ("JP6-350258") or ("JP10-022636") or ("JP2002-137328") or ("JP2002-134881") or ("JP2002-076578")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/06/26 09:27
S2	37	"5600103"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:34
S3	172	"power supply film"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:34
S4	1	"power supply film" and insulat\$4 and conduct\$4 and "b-stage"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:36

S5	4	"power supply film" and insulat\$4 and conduct\$4 and thermoset\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:36
S6	3	"power supply film" and insulat\$4 and conduct\$4 and thermoset\$4 and curing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:37
S7	4	"power supply film" and insulat\$4 and conduct\$4 and thermoset\$4 and cur \$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:37
S8	623590	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 08:43
S9	239119	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 08:44
S10	16737	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (press \$3 near9 (oxide or dielectric insulat\$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 08:47
S11	381	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (press \$3 near9 (oxide or dielectric insulat\$4)) and (b near stage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 08:48

S12	52	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (press \$3 near9 (oxide or dielectric insulat\$4)) and (b near stage) and (power near supply)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 09:45
S13	27	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (press \$3 near9 (oxide or dielectric insulat\$4)) and (b near stage) and (power near supply) and (support or frame)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 09:50
S14	11	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (press \$3 near9 (oxide or dielectric insulat\$4)) and (b near stage) and (power near supply) and (support or frame) and (plating near9 conduct\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:12
S15	3	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (pressing near9 (oxide or dielectric insulat\$4)) and (b near stage) and (power near supply) and (support or frame) and (plating near9 conduct\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:13

S16	1982	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (pressing near9 (oxide or dielectric insulat\$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:14
S17	937	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (pressing near9 (oxide or dielectric insulat\$4)) and (support or frame)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:14
S18	86	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (pressing near9 (oxide or dielectric insulat\$4)) and (support or frame) and (b near stage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:15
S19	81	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (pressing near9 (oxide or dielectric insulat\$4)) and (support or frame) and (b near stage) and ((heat\$4 or thermal) near9 (oxide or dielectric or insulat\$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/06 09:57

S20	3	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (pressing near9 (oxide or dielectric insulat\$4)) and (support or frame) and (b near stage) and ((heat\$4 or thermal) near9 (oxide or dielectric or insulat\$4)) and (power near supply)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:21
S21	128560	(conduct\$4 near9 (plating or etch\$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 14:37
S22	111747	(conduct\$4 near9 (plating or etch\$4)) and (support or base pr carrier or arm or substrate or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 14:38
S23	35038	(conduct\$4 near9 (plating or etch\$4)) and (support or base pr carrier or arm or substrate or wafer) and press\$4 and (insulat\$4 or dielectric or oxide) near9 (support or base pr carrier or arm or substrate or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 14:40
S24	7011	(conduct\$4 near9 (plating or etch\$4)) and (support or base pr carrier or arm or substrate or wafer) and press\$4 and (insulat\$4 or dielectric or oxide) near9 (support or base pr carrier or arm or substrate or wafer) and (press\$4 near9 (insulat\$4 or dielectric	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 14:41

		or oxide))				
S25	7010	(conduct\$4 near9 (plating or etch\$4)) and (support or base or carrier or arm or substrate or wafer) and press\$4 and (insulat\$4 or dielectric or oxide) near9 (support or base or carrier or arm or substrate or wafer) and (press\$4 near9 (insulat\$4 or dielectric or oxide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 14:42
S26	338	(conduct\$4 near9 (plating or etch\$4)) and (support or base or carrier or arm or substrate or wafer) and press\$4 and (insulat\$4 or dielectric or oxide) near9 (support or base or carrier or arm or substrate or wafer) and (press\$4 near9 (insulat\$4 or dielectric or oxide)) and (electronic near part)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 14:44
S27	46	(conduct\$4 near9 (plating or etch\$4)) and (support or base or carrier or arm or substrate or wafer) and press\$4 and (insulat\$4 or dielectric or oxide) near9 (support or base or carrier or arm or substrate or wafer) and (press\$4 near9 (insulat\$4 or dielectric or oxide)) and (electronic near part) and (B near stage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 15:01
S28	88010	(conduct\$4 near portion)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 09:55

S29	12774	(conduct\$4 near portion) near9 (support or base or substrate or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:52
S30	1242	(conduct\$4 near portion) near9 (support or base or substrate or wafer) and (copper near9 (insulat\$4 or oxide or dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:54
S31	55	(conduct\$4 near portion) near9 (support or base or substrate or wafer) and (copper near9 (insulat\$4 or oxide or dielectric)) and (b near stage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:54
S32	46	(conduct\$4 near portion) near9 (support or base or substrate or wafer) and (copper near9 (insulat\$4 or oxide or dielectric)) and (b near stage) and press \$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:55
S33	27	(conduct\$4 near portion) near9 (support or base or substrate or wafer) and (copper near9 (insulat\$4 or oxide or dielectric)) and (b near stage) and press \$4 and thermoplastic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:56
S34	25	(conduct\$4 near portion) near9 (support or base or substrate or wafer) and (copper near9 (insulat\$4 or oxide or dielectric)) and (b near stage) and press \$4 and thermoplastic and (heat or anneal)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:56

S35	9	(conduct\$4 near portion) near9 (support or base or substrate or wafer) and (copper near9 (insulat\$4 or oxide or dielectric)) and (b near stage) and press \$4 and thermoplastic and (heat or anneal) and (power near supply)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:56
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